

# 2SJ181(L), 2SJ181(S)

## Silicon P Channel MOS FET

R07DS0395EJ0300 (Previous: REJ03G0848-0200) Rev.3.00

## May 16, 2011

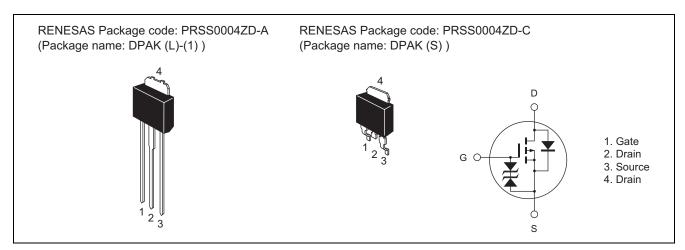
### **Description**

High speed power switching

#### **Features**

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

#### **Outline**



## **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

| Item                                      | Symbol                        | Value       | Unit |
|---|-------------------------------|-------------|------|
| Drain to source voltage                   | V <sub>DSS</sub>              | -600        | V    |
| Gate to source voltage                    | $V_{GSS}$                     | ±15         | V    |
| Drain current                             | I <sub>D</sub>                | -0.5        | A    |
| Drain peak current                        | I <sub>D (pulse)</sub> Note 1 | -1.0        | Α    |
| Body to drain diode reverse drain current | I <sub>DR</sub>               | -0.5        | Α    |
| Channel dissipation                       | Pch Note 2                    | 20          | W    |
| Channel temperature                       | Tch                           | 150         | °C   |
| Storage temperature                       | Tstg                          | -55 to +150 | °C   |

Notes: 1.  $PW \le 10 \mu s$ , duty cycle  $\le 1\%$ 

2. Value at Tc = 25°C

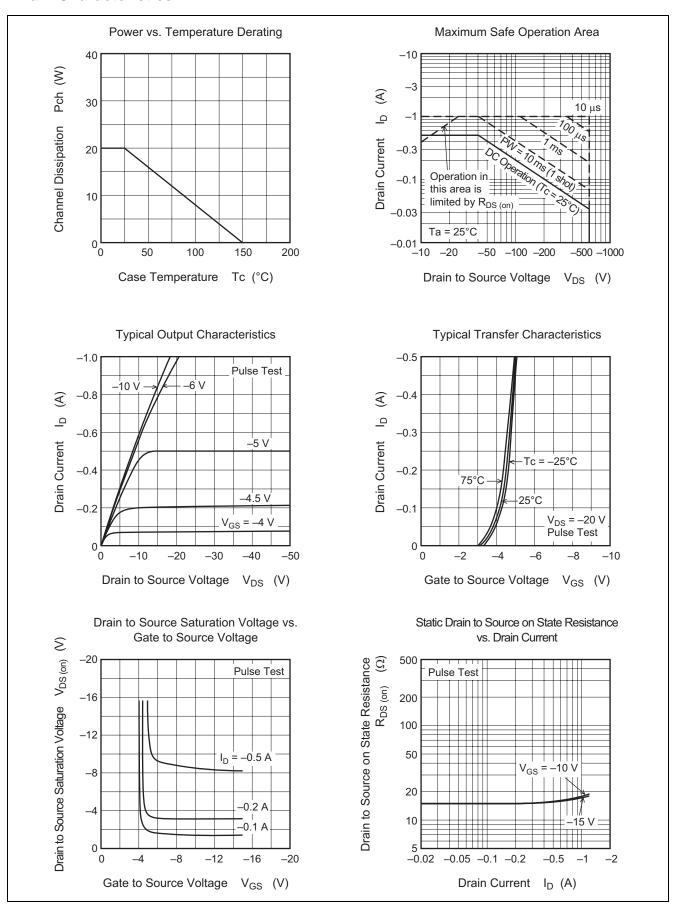
## **Electrical Characteristics**

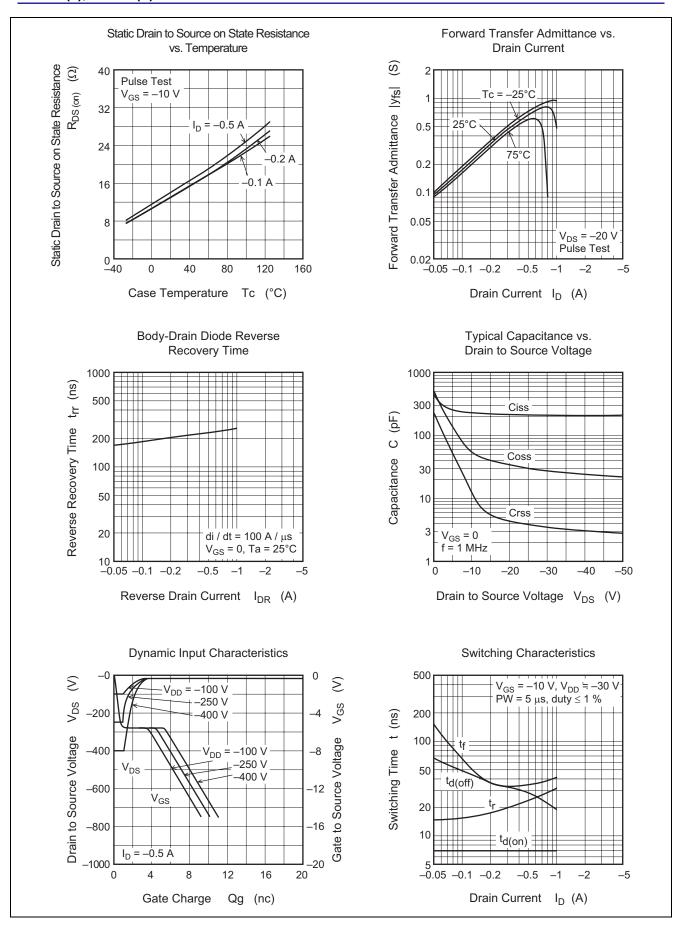
 $(Ta = 25^{\circ}C)$ 

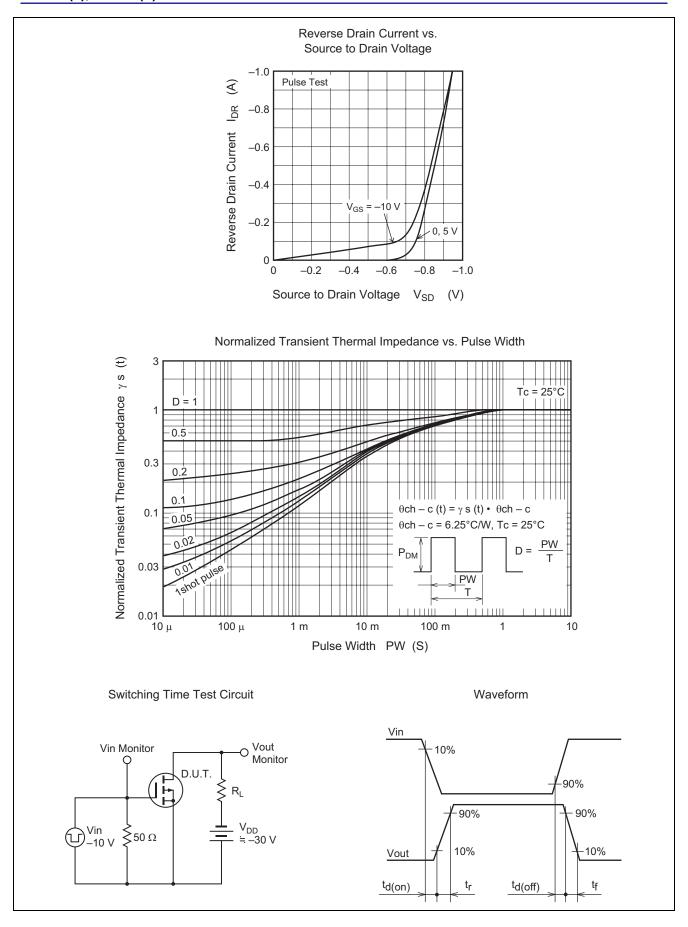
| Item                                       | Symbol                | Min  | Тур   | Max  | Unit | Test Conditions  |
|--|-----------------------|------|-------|------|------|--|
| Drain to source breakdown voltage          | V <sub>(BR) DSS</sub> | -600 | _     | _    | V    | $I_D = -10 \text{ mA}, V_{GS} = 0$                             |
| Gate to source breakdown voltage           | V <sub>(BR) GSS</sub> | ±15  | _     | _    | V    | $I_G = \pm 100 \ \mu A, \ V_{DS} = 0$                          |
| Gate to source leak current                | I <sub>GSS</sub>      | _    | _     | ±10  | μΑ   | $V_{GS} = \pm 12 \text{ V}, V_{DS} = 0$                        |
| Zero gate voltage drain current            | I <sub>DSS</sub>      | _    | _     | -100 | μΑ   | $V_{DS} = -500 \text{ V}, V_{GS} = 0$                          |
| Gate to source cutoff voltage              | V <sub>GS (off)</sub> | -2.0 | _     | -4.0 | V    | $I_D = -1 \text{ mA}, V_{DS} = -10 \text{ V}$                  |
| Static drain to source on state resistance | R <sub>DS (on)</sub>  | _    | 15    | 25   | Ω    | $I_D = -0.3 \text{ A}, V_{GS} = -10 \text{ V}^{\text{Note 3}}$ |
| Forward transfer admittance                | y <sub>fs</sub>       | 0.3  | 0.45  | _    | S    | $I_D = -0.3 \text{ A}, V_{DS} = -20 \text{ V}^{\text{Note 3}}$ |
| Input capacitance                          | Ciss                  | _    | 220   | _    | рF   | $V_{DS} = -10 \text{ V}$                                       |
| Output capacitance                         | Coss                  | _    | 55    | _    | рF   | $V_{GS} = 0$   |
| Reverse transfer capacitance               | Crss                  | _    | 13    | _    | pF   | f = 1 MHz  |
| Turn-on delay time                         | t <sub>d (on)</sub>   | _    | 7     | _    | ns   | $I_D = -0.3 \text{ A}$   |
| Rise time                                  | t <sub>r</sub>        | _    | 20    | _    | ns   | V <sub>GS</sub> = -10 V  |
| Turn-off delay time                        | t <sub>d (off)</sub>  | _    | 35    | _    | ns   | $R_L = 100 \Omega$   |
| Fall time                                  | t <sub>f</sub>        | _    | 35    | _    | ns   |  |
| Body to drain diode forward voltage        | $V_{DF}$              | _    | -0.85 | _    | V    | $I_F = -0.5 \text{ A}, V_{GS} = 0$                             |
| Body to drain diode reverse recovery time  | t <sub>rr</sub>       | _    | 230   | _    | ns   | $I_F = -0.5 \text{ A}, V_{GS} = 0$                             |
|  |                       |      |       |      |      | $di_F/dt = 50 A/\mu s$   |

Note: 3. Pulse test

#### **Main Characteristics**

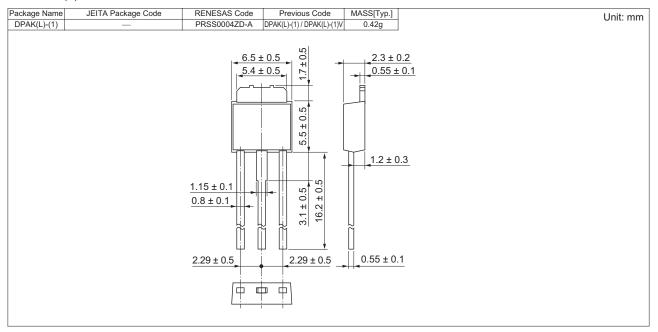




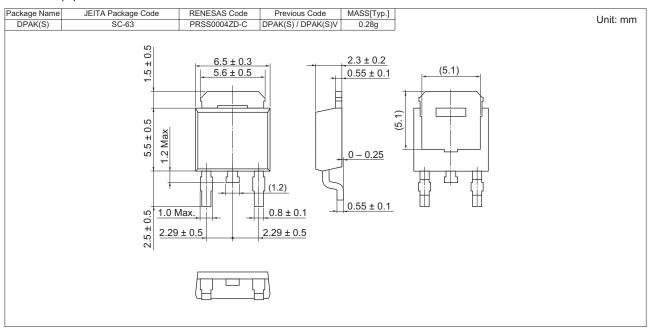


## **Package Dimensions**

#### • 2SJ181(L)



#### • 2SJ181(S)



## **Ordering Information**

| Orderable Part Number | Quantity | Shipping Container |  |  |
|-----------------------|----------|--------------------|--|--|
| 2SJ181L-E             | 2160 pcs | Box (Tube)         |  |  |
| 2SJ181STR-E           | 3000 pcs | Taping             |  |  |

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